

SILICON RECTIFIERS

12 Ampere Silicon Power Diodes

FEATURES

1N3671A

- ❖ All diffused series.
- ❖ Available in normal & reverse polarity.
- ❖ Device conforms to IS 3700 (III) & IS 4400 (III).
- ❖ Device outline conforms to IS 5000 (Do. 4) except stud.
- ❖ Available in avalanche characteristic.

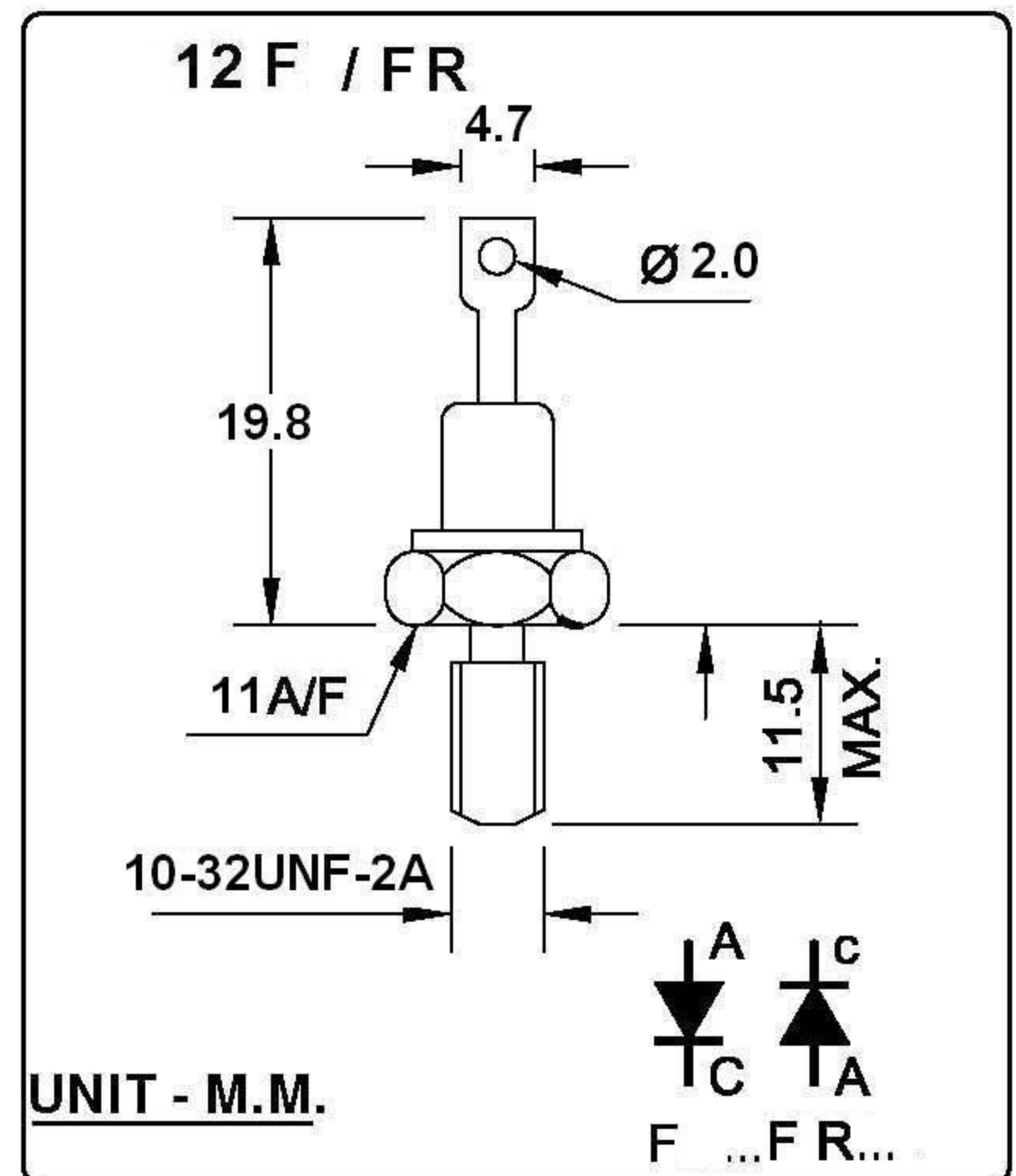
ELECTRICAL SPECIFICATIONS

12 F/FR

$I_{F(AV)}$	Maximum average forward current $T_c = 150^\circ\text{C}$	12A
V_{FM}	Maximum peak forward voltage drop @ Rated $I_{F(peak)}$ R.T.	1.35 V
I_{FSM}	Maximum peak one cycle (non-rep.) surge current 10 msec	275 A
I^2t	Max. I^2t rating (non-rep.) for 10 msec.	370 A ² Sec

THERMAL MECHANICAL SPECIFICATIONS

θ_{J-C}	Maximum thermal resistance junction to case	2°C/W
θ_{C-H}	Contact thermal resistance	0.5°C/W
T_J	Operating junction temp.	-40°C to 180°C
T_{stg}	Storage temperature	-40°C to 200°C
	Mounting torque (Non-lubricated threads)	1.36 to 1.69 Nm
W	Approx. weight	7 gms.

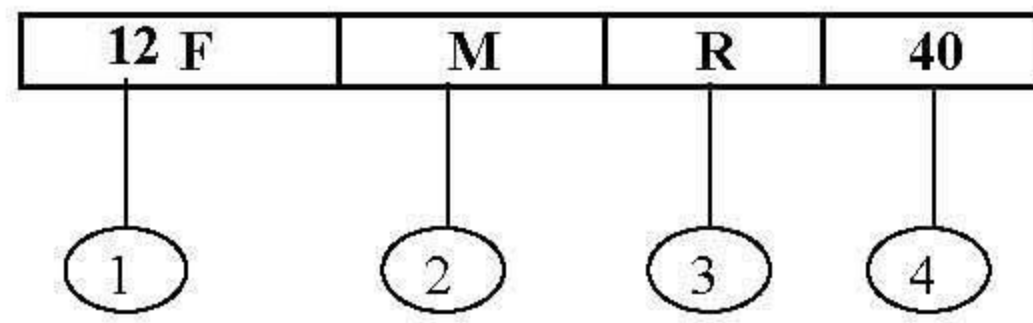


ELECTRICAL RATINGS

TYPE	NUMBER	12 F /FR	10	20	40	60	80
V_{RRM}	Max. repetitive peak reverse voltage (V)		100	200	400	600	800
V_{RSM}	Max. non-repetitive peak reverse voltage (V)		200	400	600	800	1000
$V_{R(RMS)}$	Max. R.M.S. reverse voltage (V)		70	140	280	420	560
V_R	Max. D.C. Blocking voltage (V)		100	200	400	600	800
	Recommended R.M.S. working voltage (V)		40	80	160	240	320
I_{RM}	Max. Peak reverse leakage current @ V_{RRM}, T_c (mA)		1	1	1	1	1

SILICON RECTIFIERS

Order Information Table



- | | | | | |
|---|---|--------|---|--------------------------------|
| 1 | - | 12 F | - | Essential Part No. |
| 2 | - | M - | | Stud with 6mm Metric threading |
| | | None - | | Stud with 10-32 UNF threading |
| 3 | - | None- | | Normal polarity |
| | | R - | | Reverse polarity |
| 4 | - | | | Voltage Rating (See table) |